

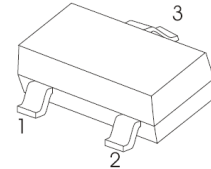
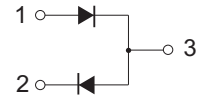


1SS226W SWITCHING DIODE

FEATURES

- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

MARKING: C3



SOT-323

Maximum Ratings ,Single Diode @Ta=25°C

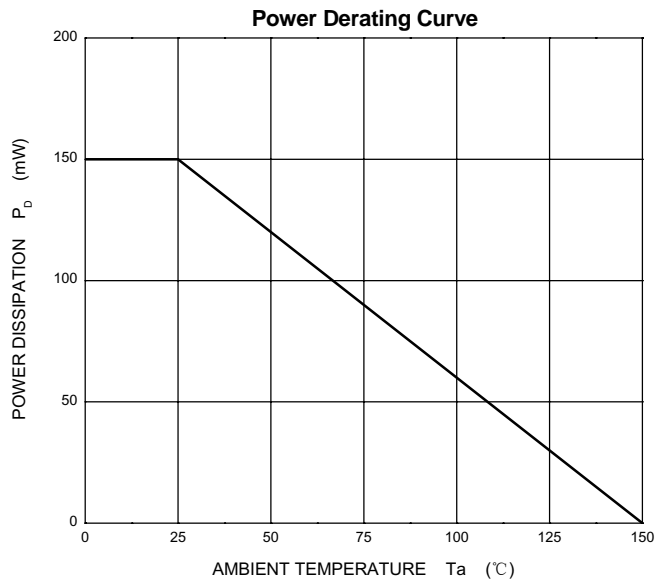
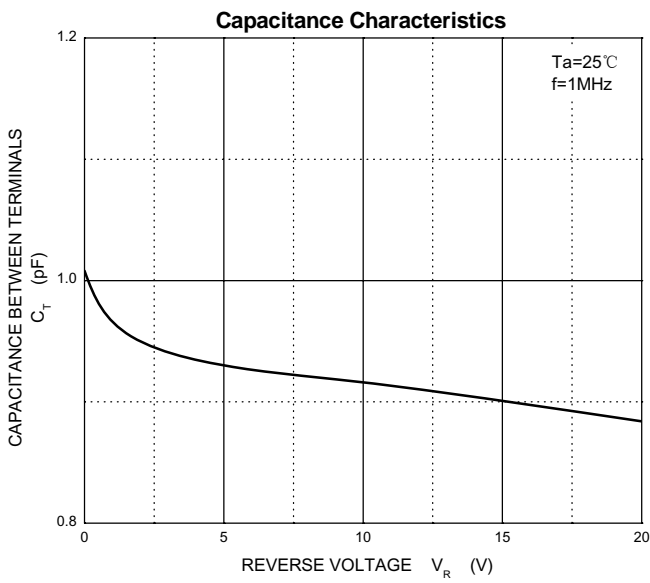
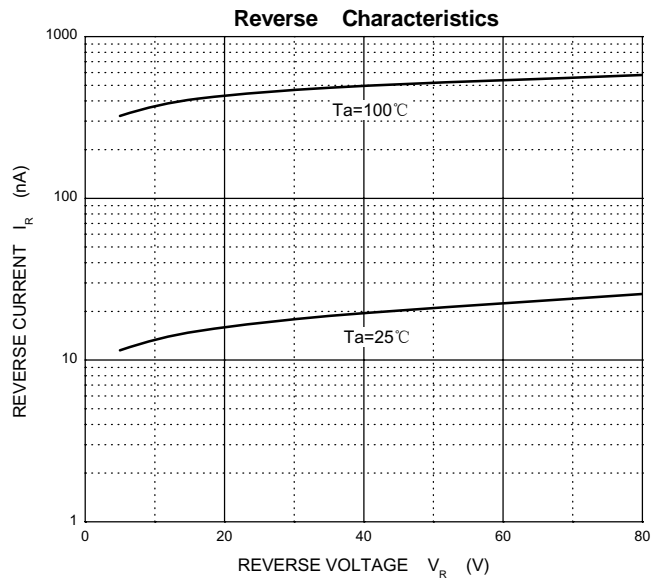
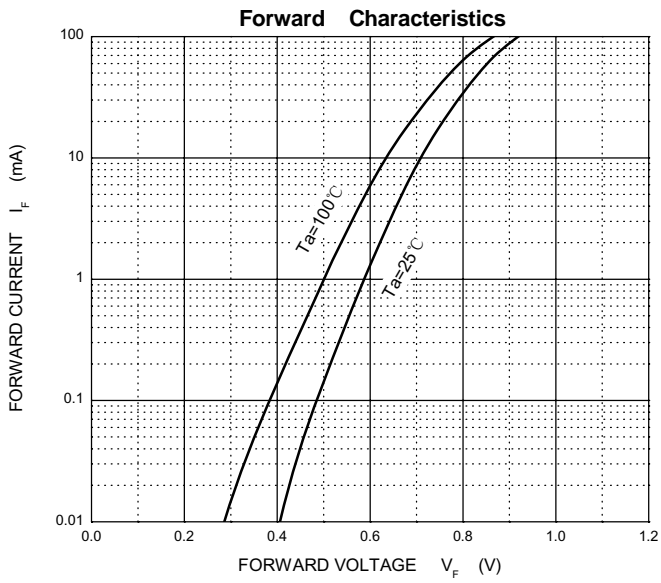
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	85	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	80	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_o	100	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse voltage leakage current	I_R	$V_R=80V$		0.5	μA
Forward voltage	V_F	$I_F=100mA$		1.2	V
Diode capacitance	C_D	$V_R=0V, f=1MHz$		3	pF
Reverse recovery time	t_{rr}	$I_F=10mA$		4	ns

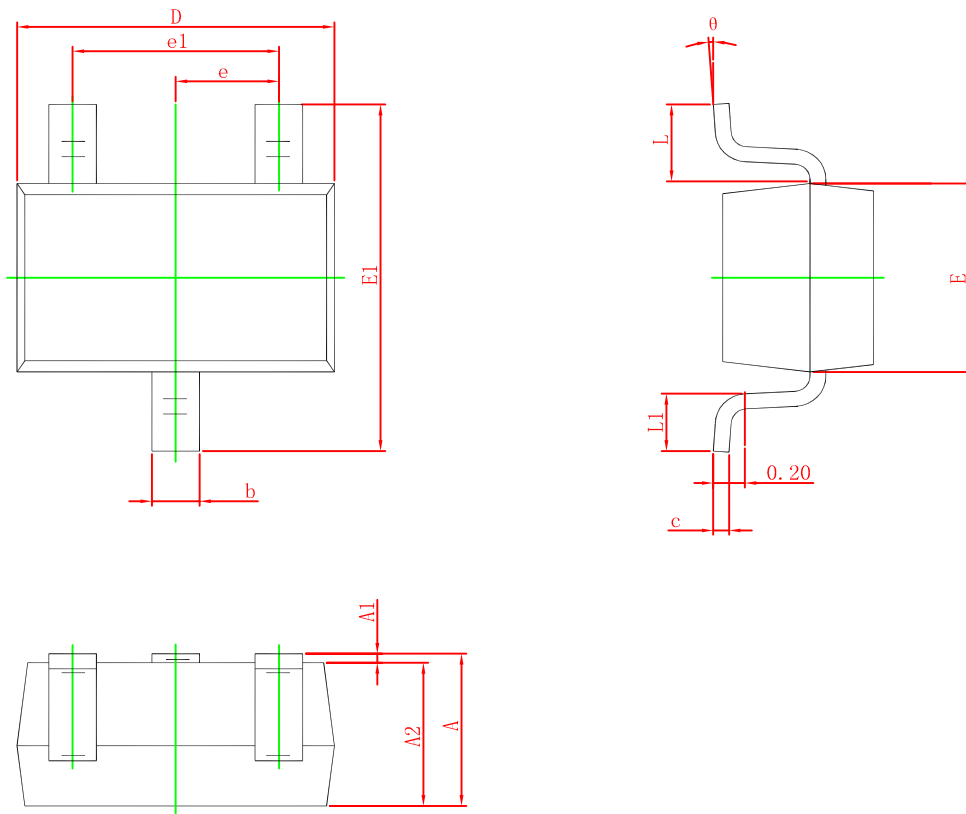


Typical Characteristics





PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
theta	0°	8°	0°	8°